

MA2B170, MA2B171

Silicon epitaxial planar type

For high-speed switching circuits

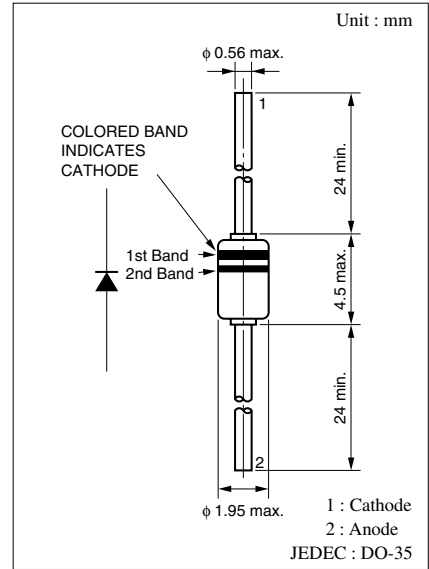
■ Features

- Large forward current $I_{F(AV)}$
- High switching speed
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	MA2B170	V_R 40	V
	MA2B171	80	
Repetitive peak reverse voltage	MA2B170	V_{RRM} 40	V
	MA2B171	80	
Average forward current	$I_{F(AV)}$	200	mA
Repetitive peak forward current	I_{FRM}	600	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	200	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +200	$^\circ\text{C}$

Note) * : $t = 1 \text{ s}$



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

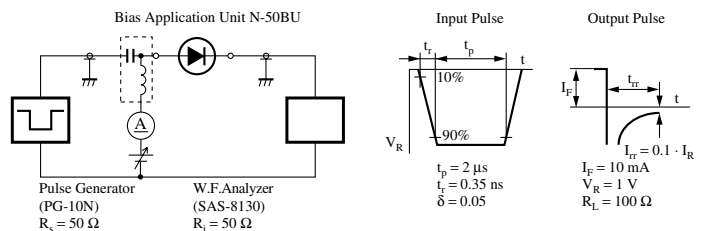
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	MA2B170	I_{R1} $V_R = 15 \text{ V}$			50	nA
	MA2B171					
	MA2B170	I_{R2} $V_R = 35 \text{ V}$ $V_R = 75 \text{ V}$			500	nA
	MA2B171				500	
	MA2B170	I_R $V_R = 35 \text{ V}, T_a = 150^\circ\text{C}$ $V_R = 75 \text{ V}, T_a = 150^\circ\text{C}$			100	μA
	MA2B171				100	
Forward voltage (DC)	V_F	$I_F = 200 \text{ mA}$			1.1	V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			4	pF
Reverse recovery time*	t_{rr}	$I_F = 10 \text{ mA}, V_R = 1 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			20	ns

Note) 1. Rated input/output frequency: 100 MHz

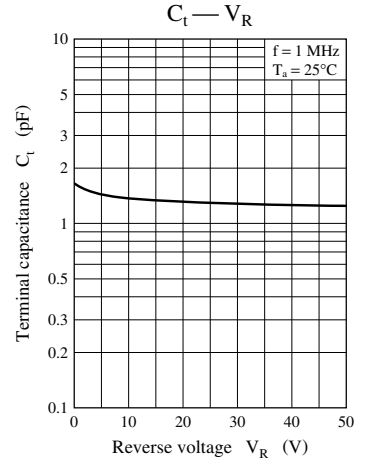
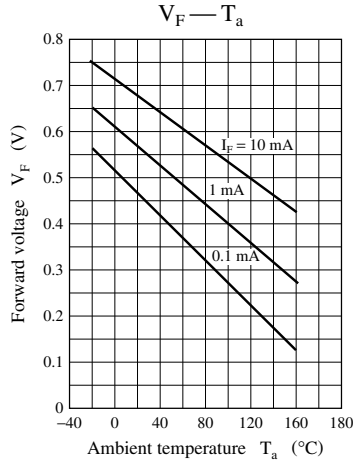
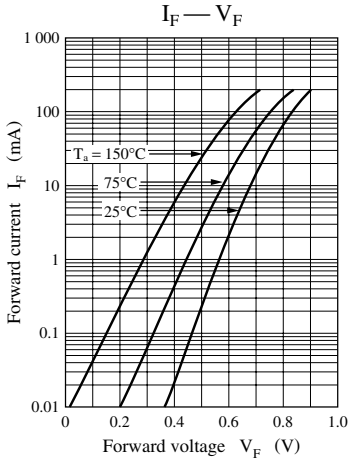
2. * : t_{rr} measuring circuit

■ Cathode Indication

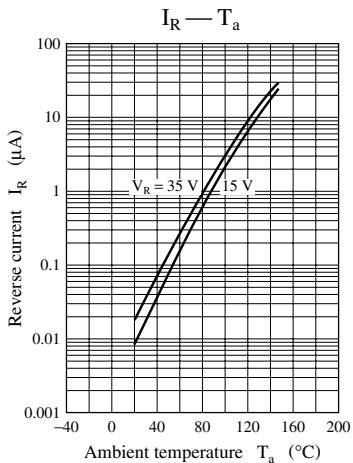
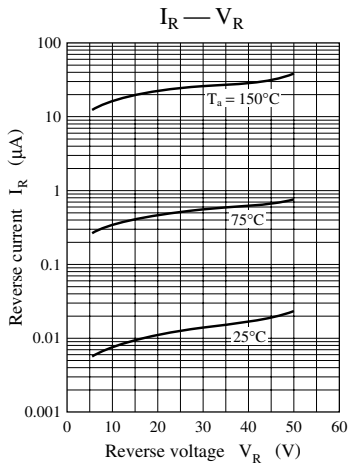
Type No.	MA2B170	MA2B171
Color		
1st Band	Violet	Violet
2nd Band	White	Green



Common characteristics charts



Characteristics charts of MA2B170



Characteristics charts of MA2B171

